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Sheet 1 of 1

Form PTO-1479 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE				ATTY. DOCKET NO. M22-2297		SERIAL NO. 10726328	
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)				APPLICANT: Gary J. Dondorson et al. 10/726328			
				FILED DATE: December 1, 2003		GROUP: Unknown	
U.S. PATENT DOCUMENTS							
Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate
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FOREIGN PATENT DOCUMENTS							
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OTHER REFERENCES (including Author, Title, Date, Page(s), Etc.)							
MW	AR			Klaus, J.W. et al., "Atomic Layer Deposition of SiO ₂ Using Catalyzed and Uncatalyzed Self-Limiting Surface Reactions",			
MW				Surface Review and Letters, Vol. 6, Nos. 3 & 4 (1999), © World Scientific Pub. Co., pp. 435-448.			
	AS						
EXAMINER			DATE CONSIDERED	6/19/2006			
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PAGE 3117 * RCVD AT 12/31/2003 12:01:24 PM (Eastern Standard Time) * SVR:USPTO-EFXXF-1/2 * DNIS:8729306 * CSID:5098383424 * DURATION (mm-ss):06-12

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Form PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. M122-2297		SERIAL NO. Filed Herewith	
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)				APPLICANT Garo J. Derderian et al.			
				FILING DATE Filed Herewith		GROUP Unknown	
U.S. PATENT DOCUMENTS							
*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
MMS	AA	6,444,495 B1	09/02	Leung et al.			
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)							
MMS	AB	Frank, M. et al., "Enhanced Initial Growth of Atomic-Layer-Deposited Metal Oxides on Hydrogen-Terminated Silicon", App. Phys. Lett., Vol. 83, No. 4, July 28, 2003, pp. 740-742.					
	AC	Rosidian, A. et al., "Formation of Ultrahard Metal Oxide Nanocluster Coatings at Room Temperature by Electrostatic Self-Assembly", SPIE Vol. 3675 (1999), pp. 113-119.					
	AD	Sakaue, H. et al., "Conformable CVD of SiO ₂ into Deep Trench Using the Digital Method", Extended Abstracts of the 22nd (1990 International) Conf. on Solid State Devices and Materials, Sendai (1990), pp. 921-924.					
	AE	Mountziaris, T. et al., "Gas-Phase and Surface Chemistry in Electronic Materials Processing", Materials Research Society Symposium Proceedings, Vol. 334, held 11/29/93 - 12/2/93, Boston, MA, pp. 1-36.					
	AF	Perez, J. et al., "Fabrication and Characterization of 4H-SiC MOS Capacitors with Atomic Layer Deposited (ALD) SiO ₂ ", IEEE 7/00, pp. 144-147.					
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	AH	Klaus, J. et al., "Atomic Layer Deposition of SiO ₂ at Room Temperature Using NH ₃ -Catalyzed Sequential Surface Reactions", Surface Science 447 (2000), pp. 81-90.					
	AI	Cameron, M. et al., "Atomic Layer Deposition of SiO ₂ and TiO ₂ in Alumina Tubular Membranes: Pore Reduction and Effect of Surface Species on Gas Transport", Langmuir 2000, 16, pp. 7435-7444.					
	AJ	Horike, Y. et al., "Filling of Si Oxide into a Deep Trench Using Digital CVD Method", App. Surface Science 46, (1990), pp. 168-174.					
MMS	AK	Wise, M. et al., "Dietlyldiethoxysilane as a New Precursor for SiO ₂ Growth on Silicon", Mat. Res. Soc. Symp. Proc. Vol. 734, (© 1994 Materials Research Society), pp. 37-43.					
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ms	AA	US2003/ 0026989 A1	Pub. 2/6/03	George et al.			07/16/02
ms	AB	US2002/ 0137260 A1	Pub. 9/26/02	Leung et al.			01/11/01
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				FILING DATE: December 1, 2003		GROUP: Unknown	
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PAGE 3/17 * RCVD AT 12/31/2003 12:01:24 PM [Eastern Standard Time] * SVR:USPTO-EFXRF-1/2 * DNIS:8729306 * CSID:5098383424 * DURATION (mm:ss):06:12

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